

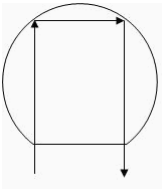
Part Number

Customer

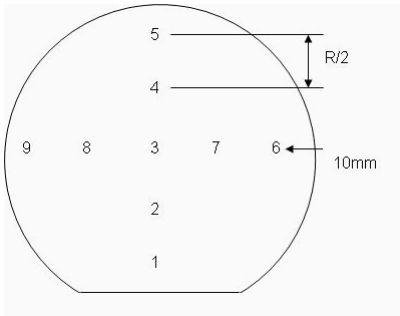
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi standard	
	5.0	Secondary Flat Length	none / 18.5mm +/-2.5mm	Wafer Vendor
	6.0	Overall Thickness	471.00 +/- 26.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	ADE 100%, SEMI MF1530.
	8.0	Bow	<60.00µm	ADE 100%, SEMI MF1390
	9.0	Warp	<60.00µm	ADE 100%, SEMI MF1390
	10.0	Edge Chips	0	Bright Light, 100%
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	14.0	Handle Thickness	300.00 +/- 25.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phos	Wafer Vendor
	17.0	Handle Resistivity	Any	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and lasermark.	Wafer Vendor
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	10,000.00 +/- 500.00 Å	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and / or device Wafer	
DeviceSilicon	22.0	Device Growth Method	FZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	24.0	Nominal Thickness	170.00 +/- 1.00 µm	100%, Single Point
	25.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phos	Wafer Vendor
	29.0	Device Resistivity	>5000 Ohm-cm	Wafer Vendor
	30.0	Voids	none	Wafer Vendor
	31.0	Scratches	0	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information